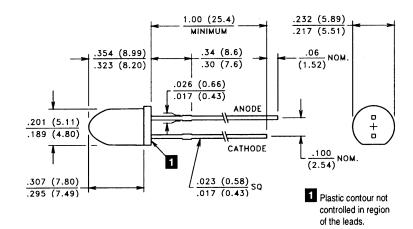
GaAlAs Infrared Emitting Diodes

T-13/4 (5 mm) Bullet Package — 880 nm

VTE1295H



PACKAGE DIMENSIONS inch (mm)



CASE 62 T-1¾ (5 mm) BULLET CHIP SIZE: .015" x .015"

DESCRIPTION

This 5 mm diameter, custom lensed device contains a medium area, single wirebonded, GaAlAs, 880 nm high efficiency IRED chip. The custom lens allows this cost effective device to have a very narrow half power beam emission of ±8°. This device is a UL recognized component for smoke alarm applications (UL file #S3506).

RoHS Compliant

ABSOLUTE MAXIMUM RATINGS @ 25°C (unless otherwise noted) ■

Maximum Temperatures		Maximum Reverse Voltage:	5.0V
Storage and Operating:	-40°C to 100°C	Maximum Reverse Current @ V _R = 5V:	10 μΑ
Continuous Power Dissipation:	200 mW	Peak Wavelength (Typical):	880 nm
Derate above 30°C:	2.86 mW/°C	Junction Capacitance @ 0V, 1 MHz (Typ.):	23 pF
Maximum Continuous Current:	100 mA	Response Time @ $I_F = 20 \text{ mA}$	•
Derate above 30°C:	1.43 mA/°C	Rise: 1.0 μs Fall: 1.0 μs	
Peak Forward Current, 10 µs, 100 pps:	2.5 A	Lead Soldering Temperature:	260°C
Temp. Coefficient of Power Output (Typ.):	8%/°C	(1.6 mm from case, 5 seconds max.)	

ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also GaAIAs curves, pages 108-110)

Part Number	Output					Forward Drop		Half Power Beam		
	Irradiance			Radiant Intensity	Total Power	Test Current	V _F		Angle	
	E _e Condition		dition	I _e	P _O	I _{FT}	@ I _{FT}		$\theta_{1/2}$	
	mW.	/cm ²	distance	Diameter	mW/sr	mW	mA	Volts		Tun
	Min.	Тур.	mm	mm	Min.	Тур.	(Pulsed)	Тур.	Max.	Тур.
VTE1295H	3.0	5.5	36	6.4	39	20	100	1.5	2.0	±8°

■ Refer to General Product Notes, page 2.

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